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November 2015

FGD5T120SH 1200 V, 5 A FS Trench IGBT

Features

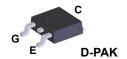
- FS Trench Technology, Positive Temperature Coefficient
- · High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)} = 2.9 V @ I_C = 5 A$
- 100% of the Parts tested for I_{I M}(1)
- · High Input Impedance
- · RoHS Compliant

Applications

- · Inrush current limitation
- · Lighting
- · Home appliances

General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 3rd generation IGBTs offer the optimum performance for inrush current limitation, lighting and home appliance applications.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		FGD5T120SH	Unit
V _{CES}	Collector to Emitter Voltage		1200	V
V_{GES}	Gate to Emitter Voltage		±25	V
V GES	Transient Gate to Emitter Voltage		±30	V
ام	Collector Current	@ T _C = 25°C	10	Α
IC	Collector Current	@ T _C = 100°C	5	А
I _{LM} (1)	Clamped Inductive Load Current	@ T _C = 25°C	12.5	А
I _{CM} (2)	Pulsed Collector Current		12.5	А
P_{D}	Maximum Power Dissipation	@ T _C = 25°C	69	W
	Maximum Power Dissipation	@ T _C = 100°C	28	W
Γ _J	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

- Notes: 1. Vcc = 600 V,V $_{GE}$ = 15 V, I $_{C}$ = 12.5 A, R $_{G}$ = 50 Ω , $\,$ Inductive Load 2. Limited by Tjmax

Thermal Characteristics

Symbol	Parameter	FGD5T120SH	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (3)	50	°C/W

Notes: 3. Mounted on 1" squre PCB (FR4 or G-10 material)

Package Marking and Ordering Information

Device Marking Device		Package	Reel Size	Tape Width	Qty per Tube	
FGD5T120SH	GD5T120SH FGD5T120SH TO-252 A03 380 mm		380 mm	16 mm	2500	

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA	1200	-	-	V
ΔBV _{CES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA	-	1.2	-	V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μА
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	± 400	nA
On Charac	teristics			•		
V _{GE(th)}	G-E Threshold Voltage	I_C = 5 mA, V_{CE} = V_{GE}	2.5	3.5	4.5	V
		I _C = 5 A, V _{GE} = 15 V	-	2.9	3.6	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 5 A, V _{GE} = 15 V, T _C = 150°C	-	4.5	-	٧
Dynamic C	Characteristics					
C _{ies}	Input Capacitance		-	209	-	pF
C _{oes}	Output Capacitance	V _{CE} = 30 V _, V _{GE} = 0 V, f = 1 MHz	-	11	-	pF
C _{res}	Reverse Transfer Capacitance	1 - 1 101112	-	2	-	pF
Switching T _{d(on)}	Characteristics Turn-On Delay Time		-	4.8	_	ns
T _r	Rise Time		-	20.8	-	ns
T _{d(off)}	Turn-Off Delay Time	V _{CC} = 600 V, I _C = 5 A,	-	24.8	-	ns
T _f	Fall Time	$R_G = 30 \Omega$, $V_{GE} = 15 V$,	-	104	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-	247	-	uJ
E _{off}	Turn-Off Switching Loss		-	94	-	uJ
E _{ts}	Total Switching Loss		-	341	-	uJ
T _{d(on)}	Turn-On Delay Time		-	4.8	-	ns
T _r	Rise Time		-	40	-	ns
T _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 5 \text{ A},$	-	25.6	-	ns
T _f	Fall Time	$R_G = 30 \Omega$, $V_{GE} = 15 V$,	-	134	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 150°C	-	393	-	uJ
E _{off}	Turn-Off Switching Loss		-	114	-	uJ
E _{ts}	Total Switching Loss		-	507	-	uJ
Qg	Total Gate Charge	$V_{CC} = 600 \text{ V}, I_{C} = 5 \text{ A},$	-	6.7	-	nC
Q_{ge}	Gate to Emitter Charge	$V_{GC} = 000 \text{ V}, I_C = 5 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	1.8	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

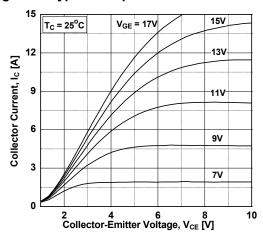


Figure 3. Typical Saturation Voltage Characteritics

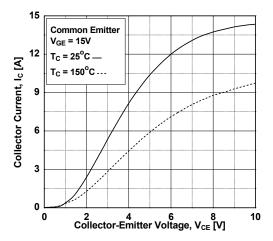


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

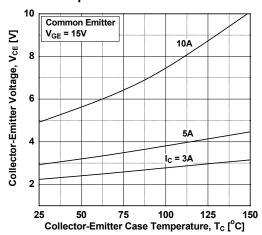


Figure 2. Typical Output Characteristics

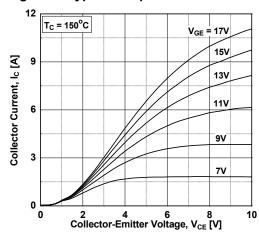


Figure 4. Transfer Characteristics

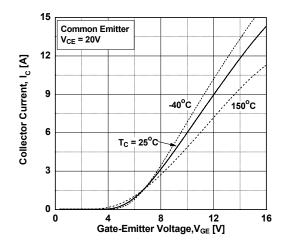
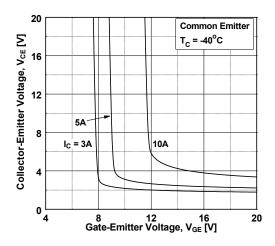


Figure 6. Saturation Voltage vs. VgE



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. VgE

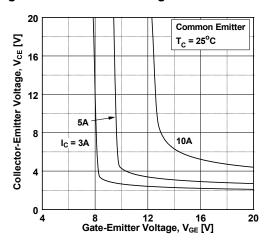


Figure 9. Capacitance Characteristics

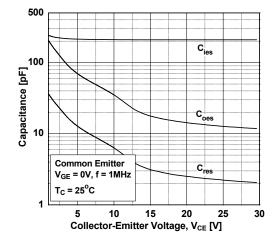


Figure 11. SOA Characteristics

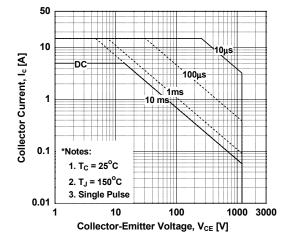


Figure 8. Saturation Voltage vs. VgE

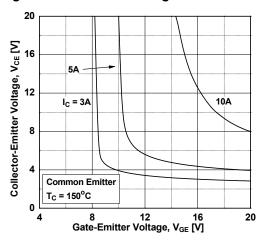


Figure 10. Gate Charge Characteristics

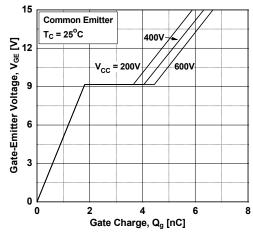
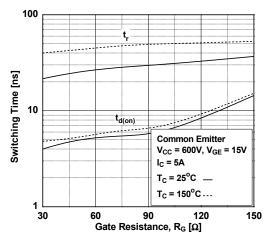


Figure 12. Turn-on Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-off Characteristics VS.
Gate Resistance

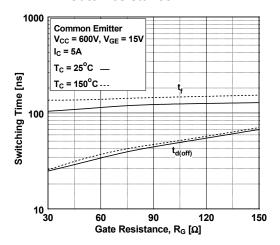


Figure 15.Turn-off Characteristics VS.
Collector Current

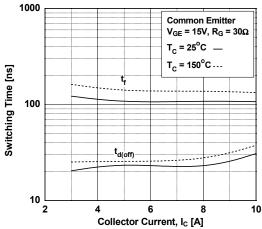


Figure 17. Switching Loss VS. Collector Current

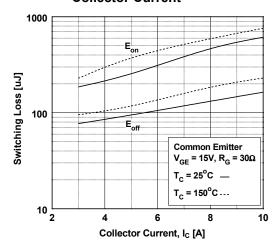


Figure 14.Turn-on Characteristics VS.
Collector Current

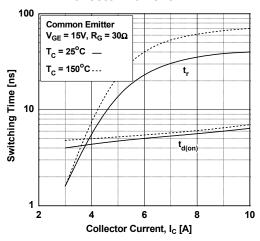


Figure 16.Switching Loss VS.
Gate Resistance

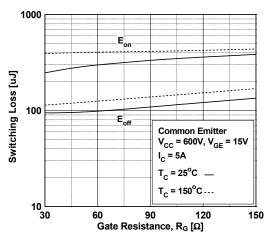


Figure 18. Current Derating

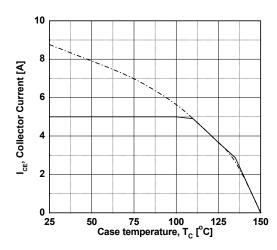


Figure 19. Load Current Vs. Frequency

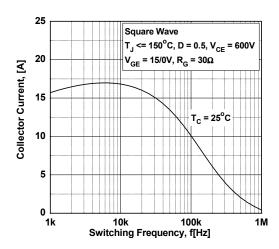
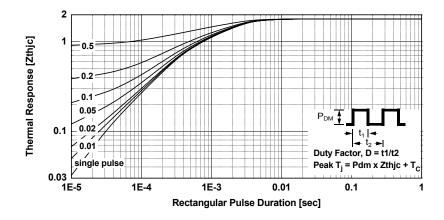


Figure 20. Transient Thermal Impedance of IGBT



6.00 MIN -6.50 MIN -1.02 MAX C 3.00 (0.59)1.40 MIN-2.30 ⊕ 0.25 M AM C 4.60 LAND PATTERN RECOMMENDATION SEE NOTE D MIN SEE 10.41 9.40 DETAIL A △ 0.10 B 0.51 GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED UNLESS OTHERWISE SPECIFIED THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994. HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION. PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL A) B) C) (1.54)E) 0.127 MAX IS OPTIONAL. IS OPTIONAL. DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD T0220P1003X238—3N. DRAWING NUMBER AND REVISION: MKT—T0252A03REV8 SEATING PLANE -(2.90) DETAIL A (ROTATED -90°) SCALE: 12X

Figure 21. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT252-003

Mechanical dimensions





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Green FPS™ Green FPS™ e-Series™ Gmax™

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Definition of Terms

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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
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